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ABSTRACT

PROBLEM - To offer a film forming apparatus and film forming method capable of applying an ALD process with high productivity without using a high-speed switching valve.

SOLUTION - The invention comprises a chamber 11 for accommodating wafers W, a substrate supporting member 12 for planar support of a plurality of wafers W inside the chamber 11, a first processing gas expelling nozzle 20 for expelling TiCl₄ and a second processing gas expelling nozzle 21 for expelling NH₃ provided inside the chamber 11, a rotation mechanism 14 for rotating the substrate supporting member 12, and a heater 16 for heating the wafer W, wherein mono-atomic Ti layers and mono-atomic N layers are alternately formed on the substrates W while rotating the substrate supporting member 12 to make the substrates W revolve.

